

DOCUMENT CHANGE REQUEST

386 DCR number Changes required for: General Originator: S Jeffery Date: 2007/10/24 Date sent: 2007/10/24 Organisation: ESA/ESTEC Status: IMPLEMENTED Title: Transistors Field-Effect N-Channel, based on types 2N4416 and 2N4416A Number: 5205/004 Issue: Other documents affected: Page: Total re-write. Paragraph: Total re-write. Original wording: Proposed wording: Total reformat of this specification as part of the ongoing conversion to the ESCC format. See below for summary of changes and attached Issue 2 Draft A of the specification. Note: Known support for active procurement against this specification includes the following manufacturers: SEMELAB/UK (not ESCC qualified but are currently willing to support the procurement of Variants 01 and 02). Summary of changes to the current format, layout and content is as follows: 1. Rewording and restructuring of various sections and paragraphs of the specification, plus other editorial changes based on the layout and editorial content of other Detail Specifications already converted to ESCC format. 2. Deletion of redundant paragraphs and information such as Mechanical Requirements. 3. Maximum Ratings table: Remark "Over entire operating temperature range" added for Drain-Source, Gate-Source and Gate-Drain voltages. 4. Maximum Ratings table: Characteristic "Total Power Dissipation (see Figure 1)" re-named "Power Dissipation" and reference to Figure 1 deleted, Remark amended from "Tamb = +25deg.C" to "Tamb <or= +25deg.C".

5. Figure 1 Parameter Derating Information moved to be a note (Note 1) to the Maximum Ratings table.

6. Para. 4.3.2 Weight requirements moved to Component Type Variants table.



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- 7. Figure 2 re-named "Physical Dimensions and Terminal Identification"; Notes revised (addition of Note 1 about Terminal Identification and Note 2 "applies to all leads" for dims. 'Ã.b', 'Ã.b2', 'L', 'L1' and 'L2').
- 8. Para. 4.2 Deviations from Generic Specification: Deviations revised/re-written per the latest ESCC Generic Specification.
- 9. Para. 4.4.1 Case requirements corrected to reflect the TO-72 metal can package.
- 10. Para. 4.4.2 Lead Material and Finish replaced by a reference to the Component Type Variants Para.
- 11. Para. 4.5.1 Required part marking corrected: Lead Identification deleted (not applicable to "TO-" packages) and ESCC qualified components symbol added.
- 12. Delete requirement for marking of the test level letter from the ESCC Component Number as per latest ESCC No. 21700.
- 13. Table 2, Characteristic "Total Gate Leakage Current" re-named "Gate Reverse Leakage Current".
- 14. Table 2, Characteristic "Gate Source Voltage" re-named "Gate-Source Forward Voltage"; Symbol corrected from VGS to VGSF; Test Method reference "See Figure 4(b)" deleted and replaced with "3403".
- 15. Table 2, Characteristic "Input Capacitance" re-named "Small-Signal Common-Source Short-Circuit Input Capacitance"; Test Conditions "VGS = 15V" and "VDS = 0V" corrected to "VDS = 15V" and "VGS = 0V".
- 16. Table 2, Characteristic "Reverse Transfer Capacitance" re-named "Small-Signal Common-Source Short-Circuit Reverse Transfer Capacitance".
- 17. Table 2, Characteristic "Modulus of Forward Transfer Admittance" re-named "Modulus of Small-Signal Common-Source Short-Circuit Forward Transfer Admittance"; Test Method 3475 and associated Test Conditions deleted; Unit corrected (was ms, now mS).
- 18. Table 2, Characteristic "Modulus of Output Admittance" re-named "Modulus of Small-Signal Common-Source Short-Circuit Output Admittance"; Test Method 3475 and associated Test Conditions deleted; Unit corrected (was µs, now µS).
- 19. Table 2, Characteristic "Power Gain (Neutralised)" re-named "Small-Signal Common-Source Insertion Power Gain (Neutralised)"; Test Method reference "See Figure 4(a)" deleted; Test Condition "RG = 1kOhm" added.
- 20. Table 2, Characteristic "Noise Factor": Symbol amended to "NF" (was "F"); Test Method reference "See figure 4(a)" deleted.
- 21. Table 2: Sampling note for AC parameters tests amended to be a fixed sample of 32 components with 0 failures (or 100%).



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- 22. Figure 4(a) corrected and moved to be a note (Note 3) to Room Temperature Electrical Measurements.
- 23. Table 3, Characteristic "Total Gate Leakage Current" re-named "Gate Reverse Leakage Current"; tolerance added to test temperature.
- 24. Table 3 (High and Low Temperature Electrical Measurements): 100% inspection has been replaced by a sample of 5 components with 0 failures, or 100%, in line with the new Generic 5000 Issue 3.
- 25. Table 4: Absolute limits have been added for information.
- 26. Table 4, Characteristic "Total Gate Leakage Current" re-named "Gate Reverse Leakage Current".
- 27. Tables 2, 3 and 4 Test Conditions column: addition of Test, or Bias, Conditions for referenced MIL-STD-750 Test Methods as and where applicable.
- 28. Table 5 amended: Tolerance added to test temperature; duration changed from being a note to a characteristic; separate paragraph "Operating Life Conditions" added.
- 29. Table 6, Characteristic "Total Gate Leakage Current" re-named "Gate Reverse Leakage Current".

Justification:

(see also change details for each item above)

- 1. Part of the ongoing activity of conversion of cover-sheeted ESA/SCC Specifications to the ESCC format.
- 2. To make the format and presentation consistent with the various other ESCC Detail Specifications already converted to ESCC format.
- 3. To make the content consistent with ESCC Generic Specification No. 5000 Issue 3.
- 4. To make corrections to technical errors in the previous issue.
- 5. Standardisation of the TO-72 package in all applicable ESCC Detail Specifications.

Attachments:
5205004_Issue_2Draft_A.pdf, null
Modifications:
The following Change Items also apply: Maximum Ratings table: Characteristic Gate-Drain Voltage amended (max. rating for Variant 01 is -30V and max. rating for Variant 02 is -35V).
Maximum Ratings table: Maximum Operating Temperature is amended (was +200, now +150).
Parameter Derating Information: Maximum Ambient Temperature is amended (was +200°C, now +150°C).
Room Temperature Electrical Measurements: Limits for Small-Signal Common-Source Short-Circuit Reverse Transfer Capacitance is amended to 0.8pF max. for both Variants.
Approval signature:
12. Cari-q
Date signed:
2007-10-24



Pages 1 to 12

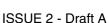
TRANSISTORS, FIELD-EFFECT, N-CHANNEL

BASED ON TYPE 2N4416 AND 2N4416A

ESCC Detail Specification No. 5205/004

Issue 2 - Draft A October 2007







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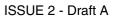
DOCUMENTATION CHANGE NOTICE

(Refer to https://escies.org for ESCC DCR content)

DCR No.	CHANGE DESCRIPTION
TBD	Specification up issued to incorporate editorial and technical changes per DCR.









<u>1.</u>	GENERAL	<u>5</u>
1.1	Scope	5
1.2	Applicable Documents	5
1.3	Terms, Definitions, Abbreviations, Symbols and Units	5
1.4	The ESCC Component Number and Component Type Variants	5
1.4.1	The ESCC Component Number	5
1.4.2	Component Type Variants	5
1.5	Maximum Ratings	5
1.6	Physical Dimensions and Terminal Identification	6
1.6.1	Metal Can Package (TO-72) - 4 lead	6
1.7	Functional Diagram	7
1.8	Materials and Finishes	7
<u>2.</u>	REQUIREMENTS	<u>8</u>
2.1	General	8
2.1.1	Deviations from the Generic Specification	8
2.2	Wafer Lot Acceptance	8
2.3	Marking	8
2.4	Terminal Strength	8
2.5	Electrical Measurements at Room, High and Low Temperatures	8
2.5.1	Room Temperature Electrical Measurements	8
2.5.2	High and Low Temperatures Electrical Measurements	11
2.6	Parameter Drift Values	11
2.7	Intermediate and End-Point Electrical Measurements	11
2.8	High Temperature Reverse Bias Burn-in Conditions	12
2.9	Operating Life Conditions	12



1. GENERAL

1.1 SCOPE

This specification details the ratings, physical and electrical characteristics and test and inspection data for the component type variants and/or the range of components specified below. It supplements the requirements of, and shall be read in conjunction with, the ESCC Generic Specification listed under Applicable Documents.

1.2 APPLICABLE DOCUMENTS

The following documents form part of this specification and shall be read in conjunction with it:

- (a) ESCC Generic Specification No. 5000
- (b) MIL-STD-750, Test Methods and Procedures for Semiconductor Devices

1.3 TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS

For the purpose of this specification, the terms, definitions, abbreviations, symbols and units specified in ESCC Basic Specification No. 21300 shall apply.

1.4 THE ESCC COMPONENT NUMBER AND COMPONENT TYPE VARIANTS

1.4.1 <u>The ESCC Component Number</u>

The ESCC Component Number shall be constituted as follows:

Example: 520500401

• Detail Specification Reference: 5205004

Component Type Variant Number: 01 (as required)

1.4.2 <u>Component Type Variants</u>

The component type variants applicable to this specification are as follows:

Variant Number	Based on Type	Case	Lead/Terminal Material and Finish	Weight max g
01	2N4416	TO-72	D2	0.9
02	2N4416A	TO-72	D2	0.9

The lead/terminal material and finish shall be in accordance with the requirements of ESCC Basic Specification No. 23500.

1.5 <u>MAXIMUM RATINGS</u>

The maximum ratings shall not be exceeded at any time during use or storage.

Maximum ratings shall only be exceeded during testing to the extent specified in this specification and when stipulated in Test Methods and Procedures of the ESCC Generic Specification.



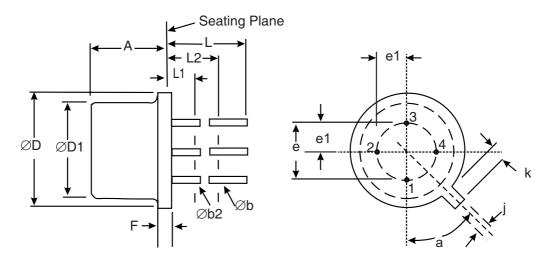
Characteristics	Symbols	Maximum Ratings	Unit	Remarks
Drain-Source Voltage	V _{DS}	30	V	Over entire
Gate-Source Voltage Variant 01 Variant 02	V _{GS}	-30 -35	V	operating temperature range
Gate-Drain Voltage	V_{GD}	-30	V	
Gate Current	I _G	10	mA	
Power Dissipation	P _{tot}	300	mW	At T _{amb} ≤ +25°C Note 1
Operating Temperature Range	T _{op}	-55 to +200	°C	
Storage Temperature Range	T _{stg}	-65 to +200	°C	
Soldering Temperature	T _{sol}	+235	°C	Note 3

NOTES:

- For T_{amb} > +25°C, derate linearly to 0W at +200°C.
 Duration 10 seconds maximum at a distance of not less than 1.5mm from the device body and the same lead shall not be resoldered until 3 minutes have elapsed.

PHYSICAL DIMENSIONS AND TERMINAL IDENTIFICATION 1.6

1.6.1 Metal Can Package (TO-72) - 4 lead



Symbols	Dimensi	Notes	
Symbols	Min	Max	Notes
Α	4.32	5.33	
Øb	0.406	0.533	2, 3
Øb2	0.406	0.483	2, 3
ØD	5.31	5.84	

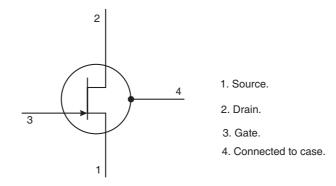


Symbols	Dimension	Notes	
Symbols	Min	Max	Notes
ØD1	4.52	4.95	
е	2.54	TP	5
e1	1.27	5	
F	-	0.762	
j	0.914	1.17	
k	0.711	1.22	4
L	12.7	-	2, 3
L1	-	1.27	2, 3
L2	6.35	-	2, 3
а	45°	5, 6	

NOTES

- 1. Terminal identification is specified by reference to the tab position where lead 1 = source, lead 2 = drain, lead 3 = gate and lead 4 = connected to the case.
- 2. Applies to all leads.
- 3. Øb2 applies between L1 and L2. Øb applies between L2 and 12.7mm from the seating plane. Diameter is uncontrolled within L1 and beyond 12.7mm from the seating plane.
- 4. Measured from the maximum diameter of the actual device.
- 5. Leads having maximum diameter 0.483mm measured in the gauging plane 1.37(+0.025,-0)mm below the seating plane of the device shall be within 0.178mm of their true position relative to a maximum-width-tab.
- 6. Measured from the tab centreline.

1.7 FUNCTIONAL DIAGRAM



1.8 MATERIALS AND FINISHES

Materials and finishes shall be as follows:

a) Case

The case shall be hermetically sealed and have a metal body with hard glass seals.



b) Leads/TerminalsAs specified in Component Type Variants.

2. REQUIREMENTS

2.1 GENERAL

The complete requirements for procurement of the components specified herein are as stated in this specification and the ESCC Generic Specification. Permitted deviations from the Generic Specification, applicable to this specification only, are listed below.

Permitted deviations from the Generic Specification and this Detail Specification, formally agreed with specific Manufacturers on the basis that the alternative requirements are equivalent to the ESCC requirement and do not affect the component's reliability, are listed in the appendices attached to this specification.

2.1.1 <u>Deviations from the Generic Specification</u>

(a) Deviation from Screening Tests - Chart F3

Power Burn-in and the subsequent Parameter Drift Values (Final Measurements) shall be omitted.

2.2 WAFER LOT ACCEPTANCE

SEM Inspection shall be performed.

2.3 MARKING

The marking shall be in accordance with the requirements of ESCC Basic Specification No. 21700 and as follows.

The information to be marked on the component shall be:

- (a) The ESCC qualified components symbol (for ESCC qualified components only).
- (b) The ESCC Component Number.
- (c) Traceability information.

2.4 <u>TERMINAL STRENGTH</u>

The test conditions for terminal strength, tested as specified in the ESCC Generic Specification, shall be as follows:

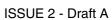
Test Condition: A, tension, with an applied force of 5 Newtons for a period of 10 seconds.

2.5 ELECTRICAL MEASUREMENTS AT ROOM, HIGH AND LOW TEMPERATURES

Electrical measurements shall be performed at room, high and low temperatures.

2.5.1 Room Temperature Electrical Measurements

The measurements shall be performed at T_{amb} =+22 ±3°C.





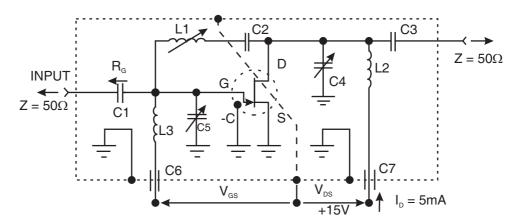
Characteristics	Symbols	MIL-STD-750	Test Conditions	Lin	nits	Units
		Test Method		Min	Max	İ
Gate Reverse Leakage Current	I _{GSS}	3411	V _{DS} =0V V _{GS} =-20V Bias condition C	-	-100	pA
Gate-Source Breakdown Voltage Variant 01 Variant 02	V _{(BR)GSS}	3401	V _{DS} =0V I _G =1μA Bias condition C	-30 -35	-	V
Gate-Source Forward Voltage	V _{GSF}	3403	V _{DS} =0V I _G =1mA	-	1	V
Gate-Source Cut- off Voltage Variant 01 Variant 02	V _{GS(off)}	3403	V _{DS} =15V I _D =1nA	- -2.5	-6 -6	V
Drain Current	I _{DSS}	3413	V _{DS} =15V Bias condition C Note 1	5	15	mA
Gate-Source Voltage	V_{GS}	3403	V _{DS} =15V I _D =500nA	-1	-5.5	V
Small-Signal Common-Source Short-Circuit Input Capacitance	C _{iss}	3431	V _{DS} =15V V _{GS} =0V f=1MHz Note 2	-	4	pF
Small-Signal Common-Source Short-Circuit Reverse Transfer Capacitance Variant 01 Variant 02	C _{rss}	3433	V _{DS} =15V V _{GS} =0V f=1MHz Note 2	-	0.9 0.8	pF
Modulus of Small- Signal Common- Source Short- Circuit Forward Transfer Admittance	IY _{21s} I	3455	V _{DS} =15V V _{GS} =0V f=1kHz Notes 1, 2	4.5	7.5	mS
Modulus of Small- Signal Common- Source Short- Circuit Output Admittance	IY _{22s} I	3453	V _{DS} =15V V _{GS} =0V f=1kHz Notes 1, 2	-	50	μS
Small-Signal Common-Source Insertion Power Gain (Neutralised)	G _P	-	V_{DS} =15 V I_{D} =5 mA R_{G} =1 $k\Omega$ f=400 MHz Notes 2, 3	10	-	dB



Characteristics	Symbols MIL-STD-750	Test Conditions	Limits		Units	
		Test Method		Min	Max	
Noise Factor	NF	-	V_{DS} =15 V I_{D} =5 mA R_{G} =1 $k\Omega$ f=400 MHz Notes 2, 3	-	4	dB

NOTES:

- 1. Pulsed measurement: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 2. For AC characteristics read and record measurements shall be performed on a sample of 32 components with 0 failures allowed. Alternatively a 100% inspection may be performed.
- 3. Small-signal common-source insertion power gain (neutralised) and noise factor shall be measured using the following test circuit.



Adjust V_{GS} for I_{D} = 5mA and V_{GS} < 0V

Capacitor	Required Value	
C1	1.8pF	
C2	27pF	
C3	1pF	
C4	0.8 - 8 pF	
C5	0.8 - 8 pF	
C6	1nF	
C7	1nF	

Inductor	Value (nH)	No. of Turns	Characteristics
L1	200	6	No. 24 enamelled copper wire, close wound on 5.563mm ceramic coil form



Inductor	Value (nH)	No. of Turns	Characteristics
L2	30	1	No. 16 enamelled copper wire, 9.525mm ID (air core)
L3	22	1/2	No. 16 enamelled copper wire, 6.35mm ID (air core)

2.5.2 High and Low Temperatures Electrical Measurements

Characteristics	Symbols	MIL-STD-750 Test Test Method Note	Test Conditions	Limits		Units
			Note 1	Min	Max	
Gate Reverse Leakage Current	I _{GSS}	3411	T _{amb} =+150(+0-5)°C V _{DS} =0V V _{GS} =-20V Bias condition C	-	-200	nA

NOTES:

1. Read and record measurements shall be performed on a sample of 5 components with 0 failures allowed. Alternatively a 100% inspection may be performed.

2.6 **PARAMETER DRIFT VALUES**

Unless otherwise specified, the measurements shall be performed at T_{amb} =+22 ±3 o C.

The test methods and test conditions shall be as per the corresponding test defined in Room Temperature Electrical Measurements.

The drift values (Δ) shall not be exceeded for each characteristic specified. The corresponding absolute limit values for each characteristic shall not be exceeded.

Characteristics	Symbols	Limits			Units
		Drift	Absolute		
		Value Δ	Min	Max	
Gate Reverse Leakage Current	I _{GSS}	±50 or (1) ±100%	-	-100	pA
Gate-Source Cut-off Voltage Variant 01	V _{GS(off)}	±10%		-6	V
Variant 02			-2.5	-6	
Drain Current	I _{DSS}	±15%	5	15	mA

NOTES:

1. Whichever is the greater referred to the initial value.

2.7 INTERMEDIATE AND END-POINT ELECTRICAL MEASUREMENTS

Unless otherwise specified, the measurements shall be performed at T_{amb} =+22 $\pm 3^{\circ}$ C.



The test methods and test conditions shall be as per the corresponding test defined in Room Temperature Electrical Measurements.

The limit values for each characteristic shall not be exceeded.

Characteristics	Symbols	Limits		Units
		Min	Max	
Gate Reverse Leakage Current	I _{GSS}	-	-100	pA
Gate-Source Cut-off Voltage	V _{GS(off)}			V
Variant 01		-	-6	
Variant 02		-2.5	-6	
Drain Current	I _{DSS}	5	15	mA

2.8 <u>HIGH TEMPERATURE REVERSE BIAS BURN-IN CONDITIONS</u>

MIL-STD-750, Test Method 1039, Condition A.

Characteristics	Symbols	Test Conditions	Units
Ambient Temperature	T _{amb}	+150(+0-5)	°C
Drain-Source Voltage	V _{DS}	0	V
Gate-Source Voltage	V _{GS}	-21	V
Duration	t	168 Minimum	Hours

2.9 <u>OPERATING LIFE CONDITIONS</u>

The conditions shall be as specified for High Temperature Reverse Bias Burn-in, except the duration shall be as specified in the ESCC Generic Specification.